

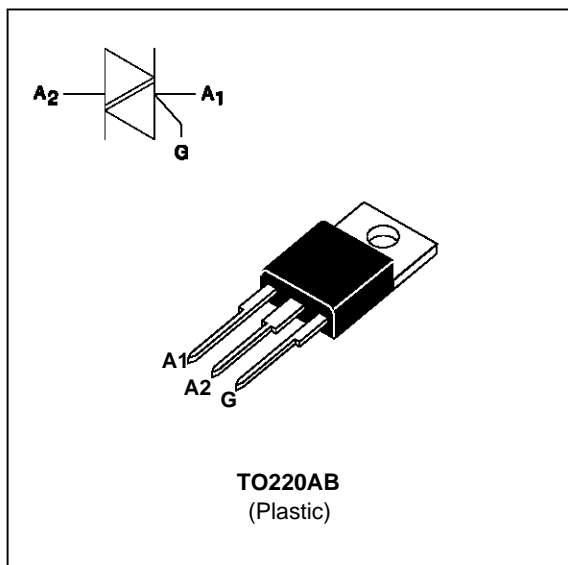
SNUBBERLESS TRIACS

FEATURES

- HIGH COMMUTATION : $(di/dt)_c > 14A/ms$ without snubber
- HIGH SURGE CURRENT : $I_{TSM} = 160A$
- V_{DRM} UP TO 800V
- BTA Family :
INSULATING VOLTAGE = 2500V_(RMS)
(UL RECOGNIZED : E81734)

DESCRIPTION

The BTA/BTB16 BW/CW triac family are high performance glass passivated chips technology. The SNUBBERLESS™ concept offer suppression of RC network and it is suitable for application such as phase control and static switching on inductive or resistive load.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit	
I _{T(RMS)}	RMS on-state current (360° conduction angle)	BTA	T _c = 80 °C	16	A
		BTB	T _c = 90 °C		
I _{TSM}	Non repetitive surge peak on-state current (T _j initial = 25°C)		tp = 8.3 ms	170	A
			tp = 10 ms	160	
I ² t	I ² t value		tp = 10 ms	128	A ² s
di/dt	Critical rate of rise of on-state current Gate supply : I _G = 500mA di _G /dt = 1A/μs		Repetitive F = 50 Hz	20	A/μs
			Non Repetitive	100	
T _{stg} T _j	Storage and operating junction temperature range		- 40 to + 150 - 40 to + 125	°C °C	
TI	Maximum lead temperature for soldering during 10 s at 4.5 mm from case		260	°C	

Symbol	Parameter	BTA / BTB16-... BW/CW				Unit
		400	600	700	800	
V _{DRM} V _{RRM}	Repetitive peak off-state voltage T _j = 125 °C	400	600	700	800	V

BTA16 BW/CW / BTB16 BW/CW

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
Rth (j-a)	Junction to ambient		60	°C/W
Rth (j-c) DC	Junction to case for DC	BTA	3.1	°C/W
		BTB	2.3	
Rth (j-c) AC	Junction to case for 360° conduction angle (F= 50 Hz)	BTA	2.3	°C/W
		BTB	1.75	

GATE CHARACTERISTICS (maximum values)

PG (AV) = 1W PGM = 10W (tp = 20 μs) IGM = 4A (tp = 20 μs) VGM = 16V (tp = 20 μs).

ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions	Quadrant		Suffix		Unit	
				BW	CW		
IGT	VD=12V (DC) RL=33Ω	Tj=25°C	I-II-III	MIN	2	1	mA
				MAX	50	35	
VGT	VD=12V (DC) RL=33Ω	Tj=25°C	I-II-III	MAX	1.5		V
VGD	VD=VDRM RL=3.3kΩ	Tj=125°C	I-II-III	MIN	0.2		V
tgt	VD=VDRM IG = 500mA dIG/dt = 3A/μs	Tj=25°C	I-II-III	TYP	2		μs
IL	IG=1.2 IGT	Tj=25°C	I-III	TYP	40	-	mA
			II	TYP	80	-	
			I-III	MAX	-	50	
			II	MAX	-	80	
IH *	IT= 500mA gate open	Tj=25°C		MAX	50	35	mA
VTM *	ITM= 22.5A tp= 380μs	Tj=25°C		MAX	1.60		V
IDRM IRRM	VDRM Rated VRRM Rated	Tj=25°C		MAX	0.01		mA
		Tj=125°C		MAX	2		
dV/dt *	Linear slope up to VD=67%VDRM gate open	Tj=125°C		MIN	500	250	V/μs
				TYP	750	500	
(di/dt)c *	Without snubber	Tj=125°C		MIN	14	8.5	A/ms
				TYP	28	17	

* For either polarity of electrode A2 voltage with reference to electrode A1.

ORDERING INFORMATION

Package	$I_T(\text{RMS})$	$V_{\text{DRM}} / V_{\text{RRM}}$	Sensitivity Specification	
	A	V	BW	CW
BTA (Insulated)	16	400	X	X
		600	X	X
		700	X	X
		800	X	X
BTB (Uninsulated)	16	400	X	X
		600	X	X
		700	X	X
		800	X	X

Fig.1 : Maximum RMS power dissipation versus RMS on-state current ($F=50\text{Hz}$).
(Curves are cut off by $(di/dt)_c$ limitation)

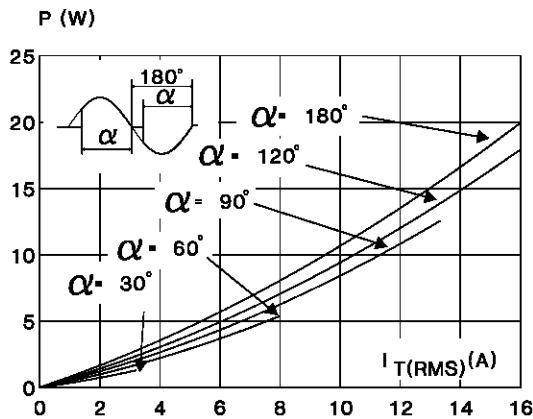


Fig.3 : Correlation between maximum RMS power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances heatsink + contact (BTB).

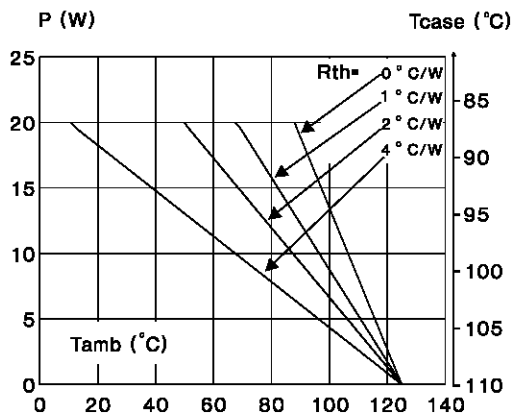


Fig.2 : Correlation between maximum RMS power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances heatsink + contact (BTA).

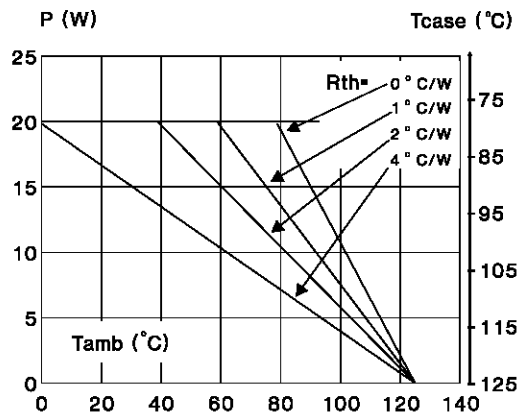
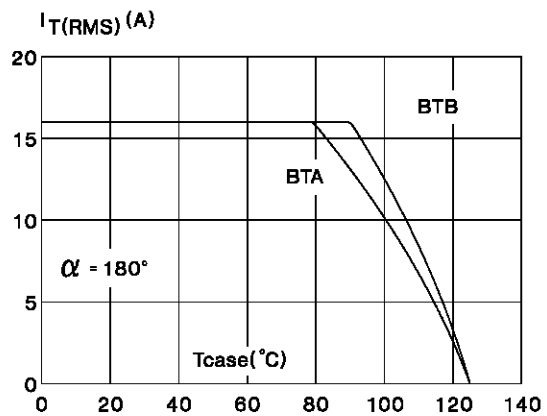


Fig.4 : RMS on-state current versus case temperature.



BTA16 BW/CW / BTB16 BW/CW

Fig.5 : Relative variation of thermal impedance versus pulse duration.



Fig.7 : Non Repetitive surge peak on-state current versus number of cycles.

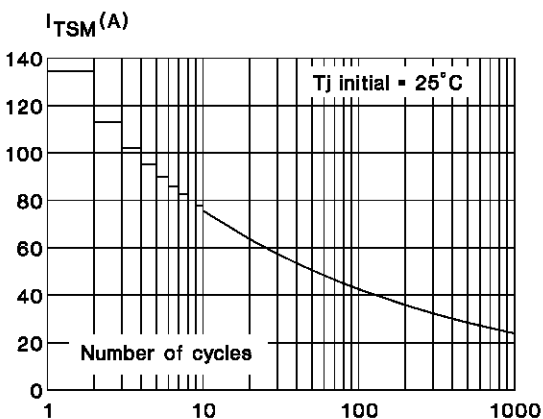


Fig.9 : On-state characteristics (maximum values).

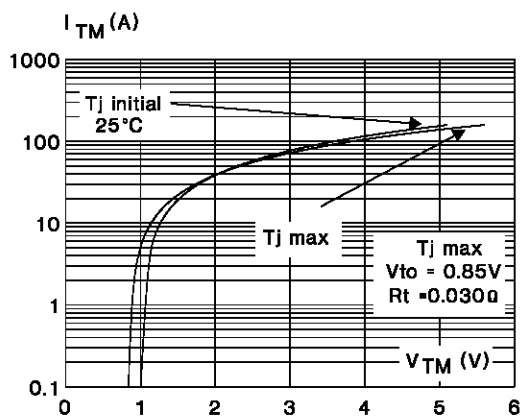


Fig.6 : Relative variation of gate trigger current and holding current versus junction temperature.

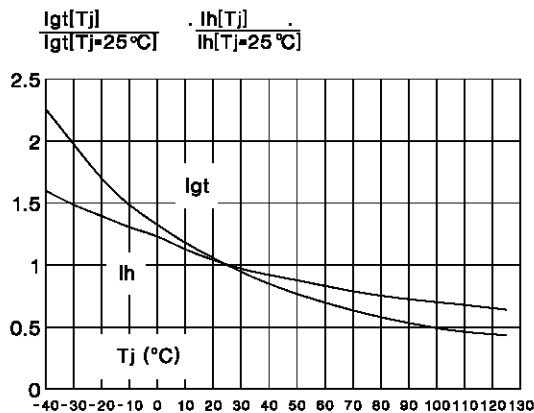
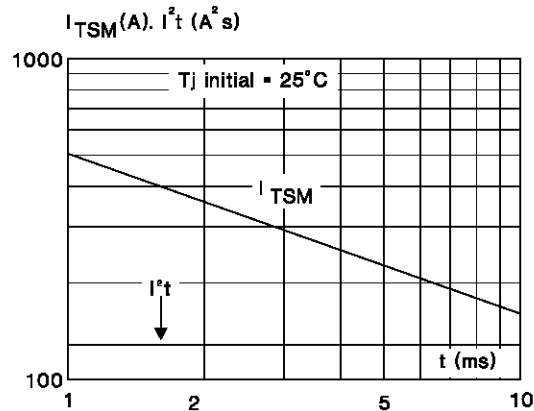
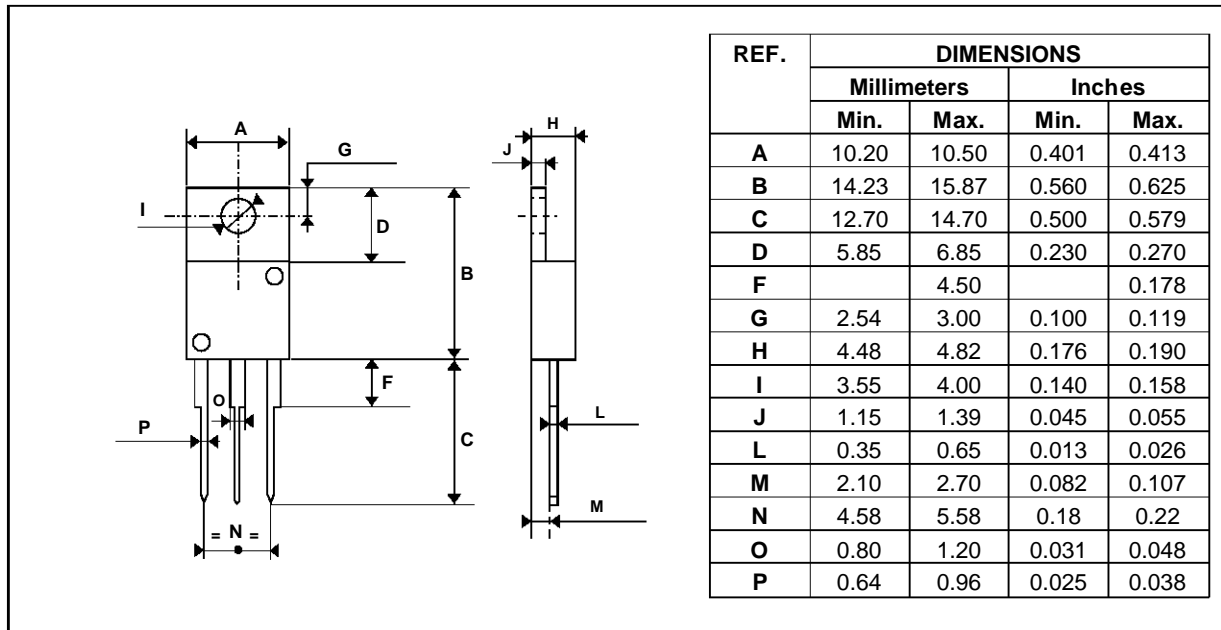


Fig.8 : Non repetitive surge peak on-state current for a sinusoidal pulse with width : $t \leq 10\text{ms}$, and corresponding value of I^2t .



PACKAGE MECHANICAL DATA

TO220AB Plastic



Cooling method : C
 Marking : type number
 Weight : 2.3 g
 Recommended torque value : 0.8 m.N.
 Maximum torque value : 1 m.N.

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